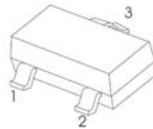


FEATURE

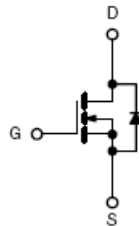
- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

SOT-23

1. GATE
2. SOURCE
3. DRAIN

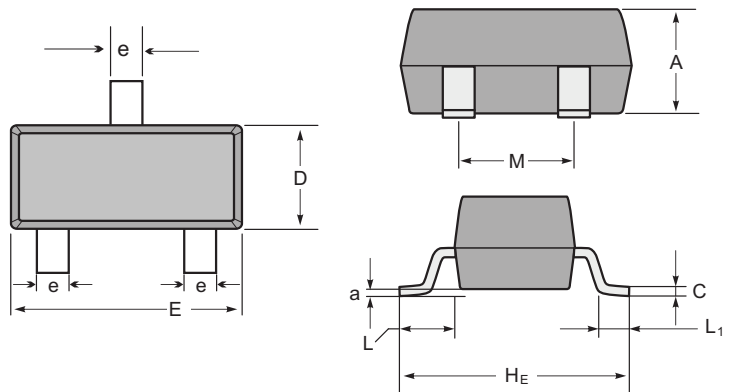


Equivalent Circuit



Marking

Type number	Marking code
SI2302	A2SHB.



SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_D	2.1	A
Continuous Source-Drain Current(Diode Conduction)	I_S	0.6	
Power Dissipation	P_D	1.2	W
Thermal Resistance from Junction to Ambient ($t \leq 5s$)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating Junction	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	

SI2302S

Electrical characteristics (T_a=25°C unless otherwise noted)

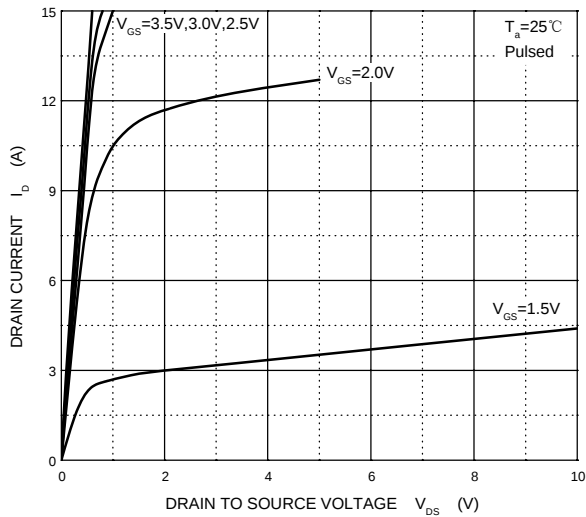
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =10μA	20			V
Gate-threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =50μA	0.65	0.95	1.2	
Gate-body leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
Drain-source on-resistance ^a	r _{DS(on)}	V _{GS} =4.5V, I _D =3.6A		0.045	0.060	Ω
		V _{GS} =2.5V, I _D =3.1A		0.070	0.115	
Forward transconductance ^a	g _{fs}	V _{DS} =5V, I _D =3.6A		8		S
Diode forward voltage	V _{SD}	I _S =0.94A,V _{GS} =0V		0.76	1.2	V
Dynamic						
Total gate charge	Q _g	V _{DS} =10V,V _{GS} =4.5V,I _D =3.6A		4.0	10	nC
Gate-source charge	Q _{gs}			0.65		
Gate-drain charge	Q _{gd}			1.5		
Input capacitance ^b	C _{iss}	V _{DS} =10V,V _{GS} =0V,f=1MHz		300		pF
Output capacitance ^b	C _{oss}			120		
Reverse transfer capacitance ^b	C _{rss}			80		
Switching ^b						
Turn-on delay time	t _{d(on)}	V _{DD} =10V, R _L =5.5Ω, I _D ≈3.6A, V _{GEN} =4.5V,R _g =6Ω		7	15	ns
Rise time	t _r			55	80	
Turn-off delay time	t _{d(off)}			16	60	
Fall time	t _f			10	25	

Notes :

- Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 2%.
- These parameters have no way to verify.

RATING AND CHARACTERISTIC CURVES (SI2302S)

Output Characteristics



Transfer Characteristics

